

**INFORMATION DISCLOSURE
CITATION**
PTO-1449

	Atty. Docket No.	Serial No.
	NTI-023-1D	Filed Herewith
	Applicant	
	LIU, Yong	
	Filing Date	Group
	Filed Herewith	

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>JZL</i>	4,231,811	11/4/1980	Somekh, et al.	148	1.5	9/13/1979
	4,426,584	1/17/1984	Bohlen, et al.	250	492.2	6/3/1981
	4,456,371	6/26/1984	Lin	355	71	6/30/1982
	4,812,962	3/14/1989	Witt	364	490	4/9/1987
	4,895,780	1/23/1990	Nissan-Cohen, et al.	430	5	10/25/1988
	4,902,899	2/20/1990	Lin, et al.	250	492.1	6/1/1987
	5,051,598	9/24/1991	Ashton, et al.	250	492.2	9/12/1990
	5,182,718	1/26/1993	Harafuji, et al.	364	490	3/29/1990
	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	5	3/19/1991
	5,241,185	8/31/1993	Meiri, et al.	250	492.2	1/8/1992
	5,242,770	9/7/1993	Chen, et al.	430	5	1/16/1992
	5,256,505	10/26/1993	Chen, et al.	430	5	8/21/1992
	5,326,659	7/5/1994	Liu, et al.	430	5	3/5/1992
	5,340,700	8/23/1994	Chen, et al.	430	312	11/3/1993
	5,432,714	7/11/1995	Chung, et al.	364	525	9/2/1994
	5,447,810	9/5/1995	Chen, et al.	430	5	2/9/1994
	5,498,579	3/12/1996	Borodovsky, et al.	437	250	6/8/1994
	5,553,273	9/3/1996	Liebmann	395	500	4/17/1995
	5,553,274	9/3/1996	Liebmann	395	500	6/6/1995
	5,572,598	11/5/1996	Wihl, et al.	382	144	2/25/1994
	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
	5,636,002	6/3/1997	Garofalo	355	53	10/31/1995
<i>AS</i>	5,657,235	8/12/1997	Liebmann, et al.	364	474.24	5/3/1995

EXAMINER:

D. Francesco

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	5,663,017	9/2/1997	Schinella, et al.	430	5	6/7/1995
	5,663,893	9/2/1997	Wampler, et al.	364	491	5/3/1995
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,705,301	1/6/1998	Garza, et al.	430	5	2/27/1996
	5,707,765	1/13/1998	Chen	430	5	5/28/1996
	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
	5,740,068	4/14/1998	Liebmann, et al.	364	489	5/30/1996
	5,766,806	6/16/1998	Spence	430	5	9/9/1996
	5,795,688	8/18/1998	Burdorf, et al.	430	30	8/14/1996
	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,804,340	9/8/1998	Garza, et al.	430	5	12/23/1996
	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
	5,821,014	10/13/1998	Chen, et al.	430	5	2/28/1997
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
	5,847,959	12/8/1998	Veneklasen, et al.	364	468.28	1/28/1997
	5,862,058	1/19/1999	Samuels, et al.	364	491	5/16/1996
	5,863,682	1/26/1999	Abe, et al.	430	30	2/21/1997
	5,879,844	3/9/1999	Yamamoto, et al.	430	30	12/20/1996
	5,885,734	3/23/1999	Pierrat, et al.	430	5	8/15/1996
	5,900,338	5/4/1999	Garza, et al.	430	5	8/15/1997
	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
	5,972,541	10/26/1999	Sugisawara, et al.	430	5	3/4/1998

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	5,994,002	11/30/1999	Matsuoka	430	5	9/4/1997
	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,009,250	12/28/1999	Ho, et al.	395	500.06	9/30/1997
	6,009,251	12/28/1999	Ho, et al.	395	500.06	9/30/1997
	6,011,911	1/4/2000	Ho, et al.	395	500.06	9/30/1997
	6,077,310	6/20/2000	Yamamoto, et al.	716	19	1/29/1999
	6,078,738	6/20/2000	Garza, et al.	395	500.22	5/8/1997
	6,081,658	6/27/2000	Rieger, et al.	395	500.22	12/31/1997
	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999
	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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<i>JCC</i>	5,282,140	1/25/1994	Tazawa, et al.	364	468	6/24/1992
	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
	6,154,363	11/28/2000	Tsudaka	382	144	12/17/1998
	6,225,025 B1	5/1/2001	Hoshino	430	296	9/22/1998
	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
	6,339,836 B1	1/15/2002	Eisenhofer, et al.	716	5	8/24/1998
	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
<i>DP</i>	2002/0076622 A1	6/20/2002	Pierrat, et al.	430	5	12/20/2000
<i>DP</i>	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

EXAMINER: J. Davalo Date Considered: 3/25/04

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<i>JRC</i>	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
	6,272,236	8/7/2001	Pierrat, et al.	382	144	7/18/2000
	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998
<i>JRC</i>	2002/0035461 A1	3/21/2002	Chang, et al.	703	13	7/16/2001

<i>JRC</i>	6,183,916	2/06/2001	Kuo et al.	430	5	9/13/1999
<i>JRC</i>	6,425,117	7/23/2002	Pasch et al.	716	21	9/29/1997

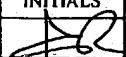
EXAMINER: J. Pascoe Date Considered: 3/25/04

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	8-236317	9/6/1996	JP			YES <input type="checkbox"/> NO <input type="checkbox"/>
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EXAMINER: E. Roasco Date Considered: 3/25/04

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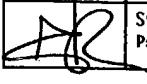
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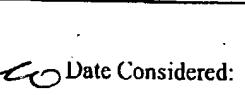
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EXAMINER'S INITIALS	CITATION		
	Ackmann, P., et al., "Phase Shifting and Optical Proximity Corrections to Improve CD Control on Logic Devices in Manufacturing for Sub 0.35 um I-Line", Advance Micro Devices (8 pages).		
	Chen, J.F., et al., "Optical Proximity Correction for Intermediate-Pitch Features Using Sub-Resolution Scattering Bars", MicroUnity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16.		
	Chen, J.F., et al., "Practical Method for Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages).		
	Cobb, et al., "Fast Sparse Aerial Image Calculation for OPC", SPIE, Vol. 2621, pp. 534-544.		
	Lithas, "Lithas: Optical Proximity Correction Software" (2 pages).		
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	Precim, "Proxima System", Precim Company, Portland, Oregon (2 pages).		
	Precim, "Proxima Wafer Proximity Correction System", Precim Company, Portland, Oregon (2 pages).		
	Rieger, M., et al., "Mask Fabrication Rules for Proximity-Corrected Patterns", Precim Company, Portland, Oregon (10 pages).		
	Rieger, M., et al., "Using Behavior Modeling for Proximity Correction", Precim Company, Portland, Oregon (6 pages).		
	Stirmiman, J., et al., "Spatial Filter Models to Describe IC Lithographic Behavior", Precim Corporation, Portland, Oregon (10 pages).		
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	Stirmiman, J., et al., "Quantifying Proximity and Related Effects in Advanced Wafer Processes", Precim Company, Hewlett Packard Labs (9 pages).		

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	Granik, Y., et al., "MEEF as a Matrix", Mentor Graphics Corporation (11 pages).		
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	Matsuura, S., et al., "Reduction of Mask Error Enhancement Factor (MEEF) by the Optimum Exposure Dose Self-Adjusted Mask", NEC Corporation (12 pages).		
	Adam, K., et al., "Simplified Models for Edge Transitions in Rigorous Mask Modeling", University of California Berkeley (40 pages).		
	Gordon, R., et al., "Mask Topography Simulation for EUV Lithography", FINLE Technologies Inc. (15 pages).		
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	Saleh, B., et al., "Reduction of Errors of Microphotographic Reproductions by Optimal Corrections of Original Masks", Optical Engineering, Vol. 20, No. 5, pp. 781-784, September/October 1981.		
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	Lin, B.J., "Methods to Print Optical Images at Low-k Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990).		

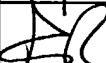
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EXAMINER'S INITIALS	CITATION		
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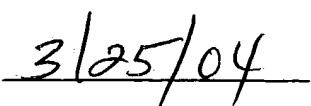
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	Ibsen, K., et al., "Clear Field Reticle Defect Deposition for Advanced Sub-Half Micron Lithography", SPIE, Proceedings Of The 17th Annual Symposium On Photomask Technology And Management, Vol. 3236, pp. 124-135 (1997).		
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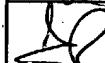
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INFORMATION DISCLOSURE CITATION		Atty. Docket No.	Serial No.
		NTI-023-1D	Filed Herewith
		Applicant	
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PTO-1449		Filing Date	Group
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		Filing Date Filed Herewith	Group
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EXAMINER'S INITIALS <i>[Signature]</i>	CITATION		
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